

**SuperMOS –SOT-23 30V  $V_{DSS}$ ,  $34m\Omega R_{DS(ON)}$ , N-channel MOSFET**

**1. Description**

The IRLML6344TRPBF-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product IRLML6344TRPBF-ES is Pb-free.

**2. Features**

- 30V,  $R_{DS(ON)}=34m\Omega(Typ.) @V_{GS}=10V$   
 $R_{DS(ON)}=50m\Omega(Typ.) @V_{GS}=4.5V$
- Use trench MOSFET technology
- High density cell design for low  $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

**3. Applications**

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

**4. Ordering Information**

Part Number	Package	Marking	Material	Packing	Quantity per Reel	Flammability Rating	Reel Sizes
IRLML6344TRPBF-ES	SOT-23	3406	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

**5. Pin Configuration and Functions**

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$BV_{DSS}$	30	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current	$I_D$	$T_A=25^{\circ}C$	4.3
		$T_A=75^{\circ}C$	3.3
Maximum Power Dissipation	$P_D$	1.4	W
Pulsed Drain Current	$I_{DM}$	17.2	A
Operating Junction Temperature	$T_J$	150	°C
Lead Temperature	$T_L$	260	°C
Storage Temperature Range	$T_{stg}$	-55 to 150	°C

### Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ( $t \leq 10s$ )	$R_{\theta JA}$		90	°C/W

## Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$			1	$\mu A$
Gate-to-source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.4	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=3.6A$		34	43	m $\Omega$
		$V_{GS}=4.5V, I_D=2.8A$		50	70	
Forward transconductance	$g_{fs}$	$V_{DS}=5V, I_D=3.6A$			40	S
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, f=1MHz,$ $V_{DS}=15V$		170		pF
Output Capacitance	$C_{OSS}$			35		
Reverse Transfer Capacitance	$C_{RSS}$			25		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=15V,$ $I_D=3.6A$		4.1		nC
Gate-to-Source Charge	$Q_{GS}$			0.6		
Gate-to-Drain Charge	$Q_{GD}$			1		
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=10V, V_{DS}=15V,$ $RL=2.2\Omega, R_G=3\Omega$		4.5		ns
Rise Time	$t_r$			1.5		
Turn-Off Delay Time	$t_{d(OFF)}$			18.5		
Fall Time	$t_f$			15.5		
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=3.6A$			1.5	V

7. Typical Characteristic

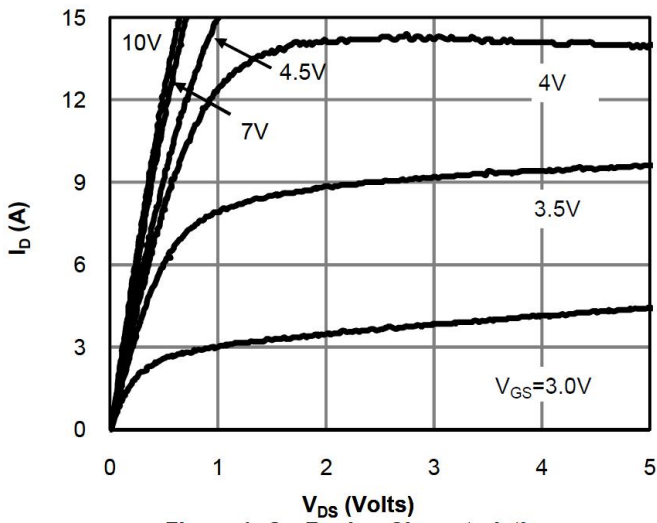


Figure 1: On-Region Characteristics

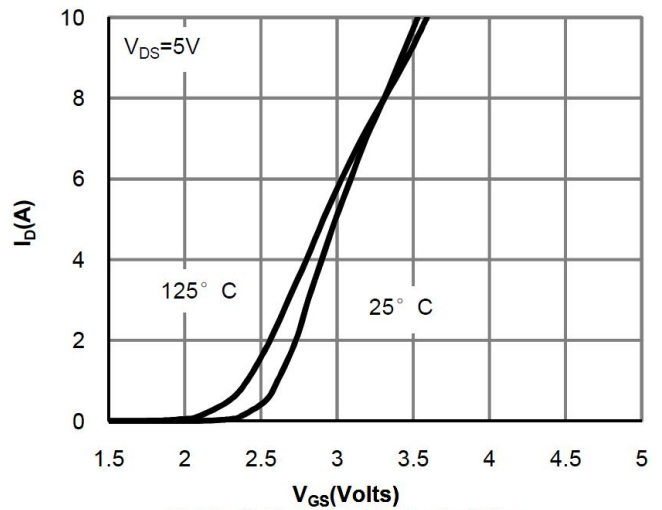


Figure 2: Transfer Characteristics

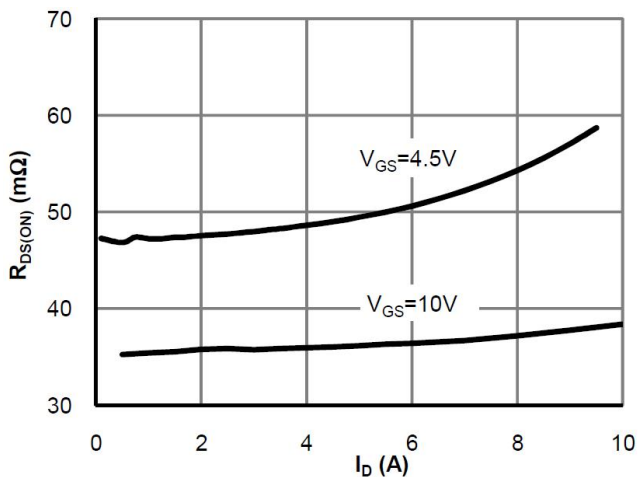


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

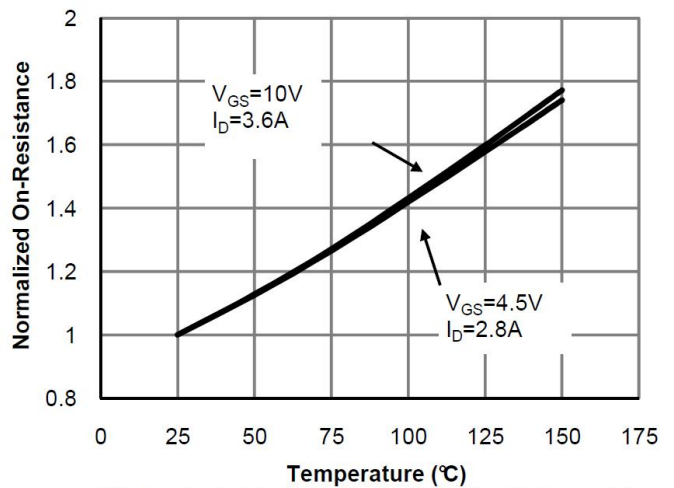


Figure 4: On-Resistance vs. Junction Temperature

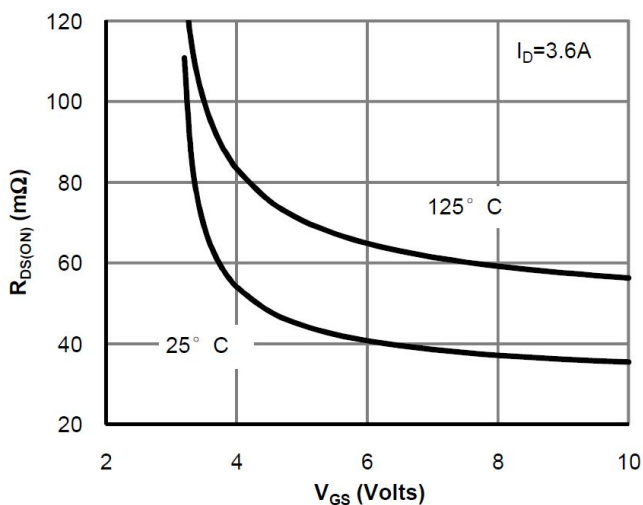


Figure 5: On-Resistance vs. Gate-Source Voltage

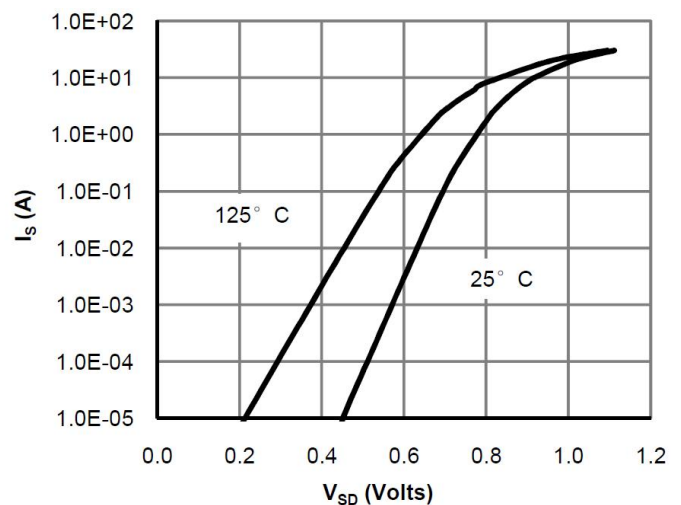
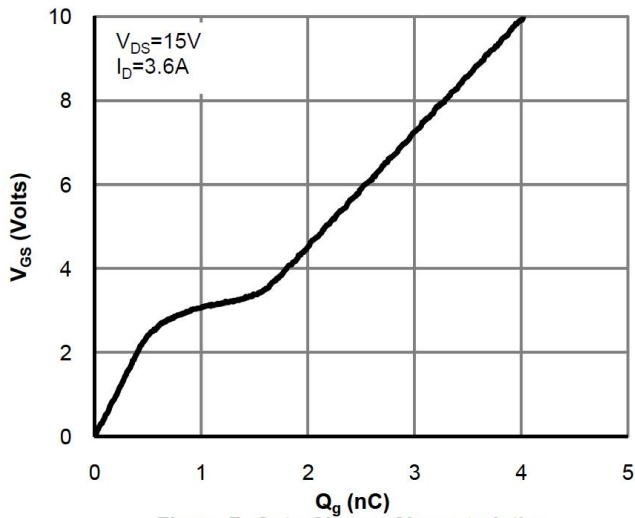
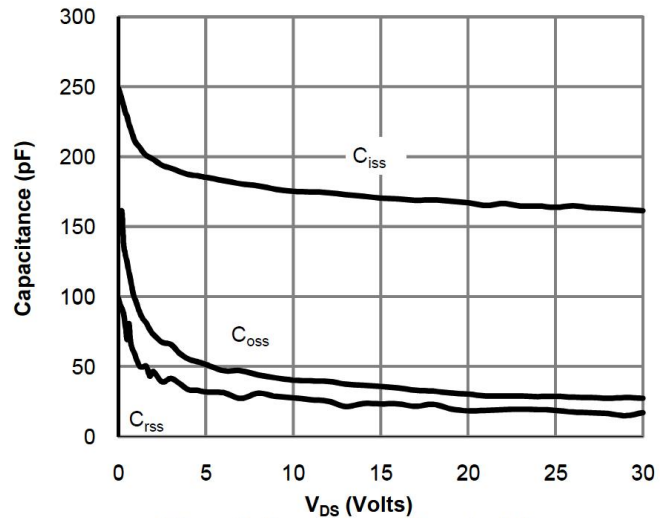


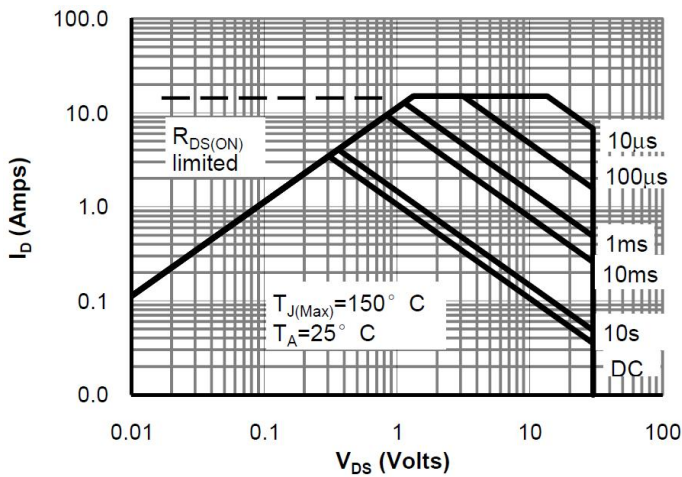
Figure 6: Body-Diode Characteristics



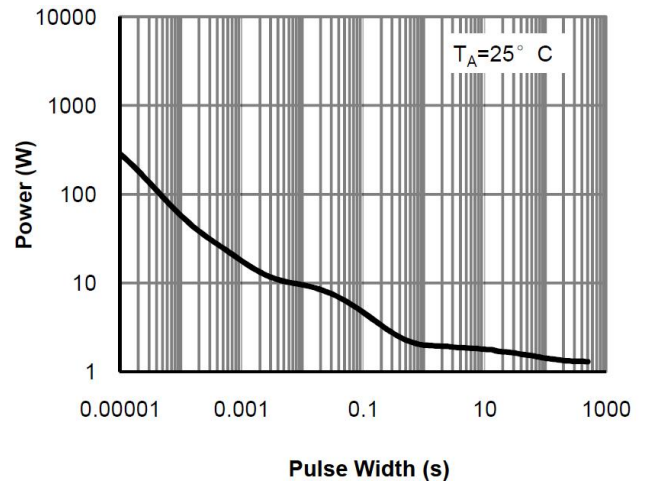
**Figure 7: Gate-Charge Characteristics**



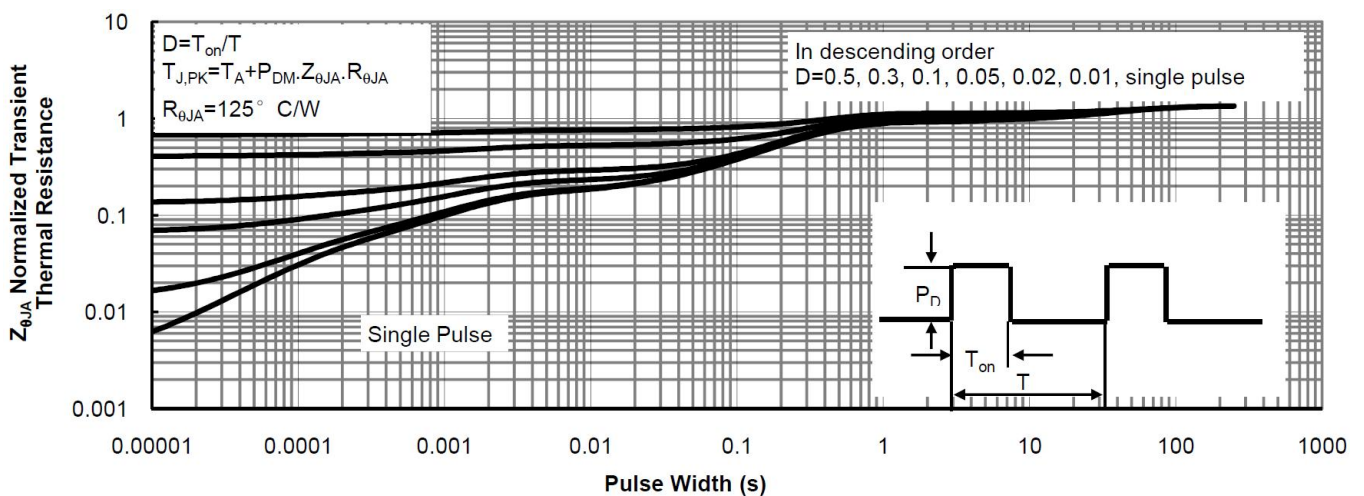
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area**

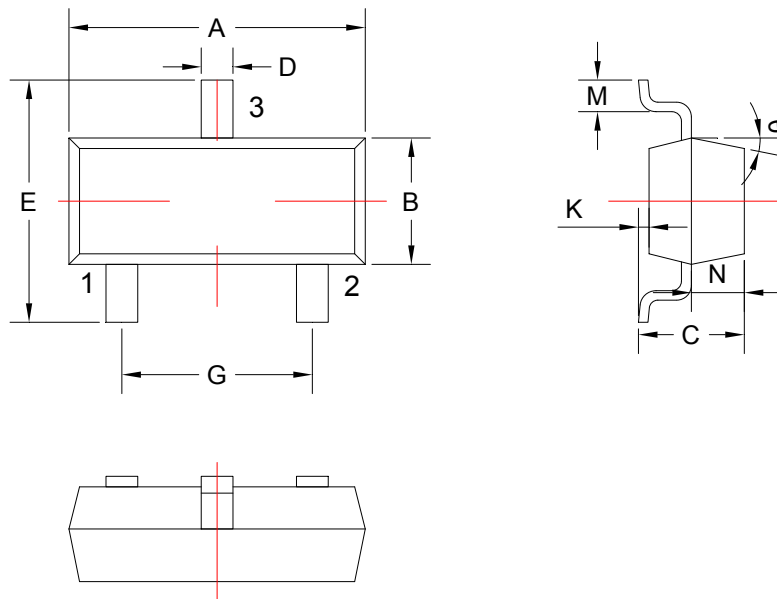


**Figure 10: Single Pulse Power Rating Junction-to-Ambient**



**Figure 11: Normalized Maximum Transient Thermal Impedance**

8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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